

invention, a disk drive has a read element including a high resistance soft magnetic layer disposed between at least one insulating layer and a magnetic shield.

[0017] Referring to FIG. 1, a magnetic disk drive 100 has at least one rotatable magnetic disk 102 supported by a spindle 104 and rotated by a motor (not shown). There is at least one slider 106 with an attached recording head 108 positioned over the disk 102 surface while reading and writing. The recording head 108 includes a write element for writing data onto the disk 102. The recording head also includes a magnetoresistive sensor according to the present invention (shown in detail below) used as a read element for reading data from the disk. The magnetoresistive sensor is responsive to an external magnetic field such as the field from a written transition on the magnetic disk 102. The slider 106 is attached to a suspension 110 and the suspension 110 is attached to an actuator 112. The actuator 112 is pivotally attached 114 to the housing 116 of the disk drive 100 and is pivoted by a voice coil motor 118. As the disk rotates, the actuator 112 positions the slider 106 along with the suspension 110 along a radial arcuate path 120 over the disk 102 surface to access a data track of interest.

[0018] Again referring to FIG. 1, during operation of the disk drive 100, the motion of the rotating disk 102 relative to the slider 106 generates an air bearing between the slider 106 and the disk 102 which exerts an upward force on the slider 106. This upward force is balanced by a spring force from the suspension 110 urging the slider 106 toward the surface of the disk 102. Alternatively, the slider 106 may be in either partial or continuous contact with the disk 102 surface during operation.

[0019] FIG. 2 illustrates a more detailed view of a slider 200. The recording head 220 is typically constructed on the trailing surface 202 of the slider 200. FIG. 2 illustrates the upper pole 204 and the turns 206 of the coil 208 of the write element 210 of the recording head 220. The read sensor 212 is disposed between the slider 200 and the write element 210. The most active portion of the read sensor 212 is revealed on the disk facing surface 215 of the slider 200. The read sensor 212 is also disposed between two magnetic shields 214. The magnetic shields 214 are typically formed from a nickel-iron alloy. The magnetic shields 214, the read sensor 212, and any intervening layers comprise the read element 216. The electrical connection pads 218 which allow connection with the write element 210 and read element 216 are illustrated.

[0020] FIG. 3 illustrates an enlarged view of a read element 300 according to the prior art. The multiple layers in the sensor stack 302 are typically abutted with magnetic hard bias and lead structures 304. The sensor stack 302 is disposed between two magnetic shields 306. There are two insulating layers 308, typically formed from alumina, silicon oxide, silicon nitride, tantalum oxide, or the like, which insulate the sensor stack 302 from each of the magnetic shields 306. The magnetic read gap 310 is the distance between the two magnetic shields 306 in the vicinity of the sensor stack 302. As mentioned previously, in order to support higher recorded densities, the read gap 310 must be reduced. The sensor stack 302 cannot be significantly reduced in thickness without degrading sensor performance. Therefore, the thickness of the insulating layers 308 have been progressively reduced. A typical thickness of an insu-

lating layer is less than 200 Angstroms and in the near future will be required to become much thinner. However the insulating layers 308 are now so thin that uniformity, susceptibility to minor defects, and the ability to withstand electrostatic damage are becoming significant problems.

[0021] FIG. 4a illustrates an embodiment of a read element 400 according to the present invention. The read element 400 includes a sensor stack 402 with abutted hard bias and lead structures 404. The sensor stack 402 is disposed between two magnetic shields 405, 406 and there are insulating layers 407, 408 disposed between the sensor stack 402 and the magnetic shields 405, 406. The insulating layers 407, 408 are typically formed from alumina, silicon oxide, silicon nitride, tantalum oxide, or the like. The magnetic shields 405, 406 are typically formed from a nickel-iron alloy such as permalloy. The read element 400 includes two layers 414, 415 of high resistance soft magnetic material disposed between each of the insulating layers 407, 408 and the magnetic shields 405, 406.

[0022] FIG. 4b illustrates another embodiment of the present invention. The read element 400 includes a sensor stack 402 with abutted hard bias and lead structures 404. The sensor stack 402 is disposed between two magnetic shields 405, 406 and there are insulating layers 407, 408 disposed between the sensor stack 402 and each of the magnetic shields 405, 406. The read element 400 includes a layer 414 of high resistance soft magnetic material disposed between the bottom insulating layer 407 and the bottom magnetic shield 405.

[0023] FIG. 4c illustrates a third embodiment of the present invention. The read element 400 includes a sensor stack 402 with abutted hard bias and lead structures 404. The sensor stack 402 is disposed between two magnetic shields 405, 406 and there are insulating layers 407, 408 disposed between the sensor stack 402 and each of the magnetic shields 405, 406. The read element 400 includes a layer 415 of high resistance soft magnetic material disposed between the top insulating layer 408 and the top magnetic shield 406.

[0024] Preferably, the resistivity of the high resistance soft magnetic material is high enough to significantly retard current through the material. The resistivity is preferably greater than about 2000 micro-ohm-cm. In addition, the magnetic moment of the high resistance soft magnetic material is preferably high enough such that the material functions as a magnetic shield without magnetically saturating. The magnetic moment of the high resistance soft magnetic material is preferably greater than about 80 emu/cc. The material preferably has a permeability greater than about 200 to function well as a magnetic shield. Finally, the high resistance magnetic material should be magnetically soft preferably having a coercivity less than about 10 Oe.

[0025] There are several materials which meet these criterion. The composition of effective materials is conveniently represented by A-B-C where A is selected from the group of iron (Fe) and cobalt (Co), B is selected from the group of hafnium (Hf), yttrium (Y), tantalum (Ta) and zirconium (Zr), and C is selected from the group of oxygen (O) and nitrogen (N). Cobalt-iron-hafnium-oxygen (CoFe-HfO) is also suitable. FeHfN is particularly suitable since the magnetic moment of FeHfN is higher than the moment of the conductive magnetic shields (405, 406 in FIGS. 4a, 4b and 4c). The magnetic shields are typically formed from